

Abstract

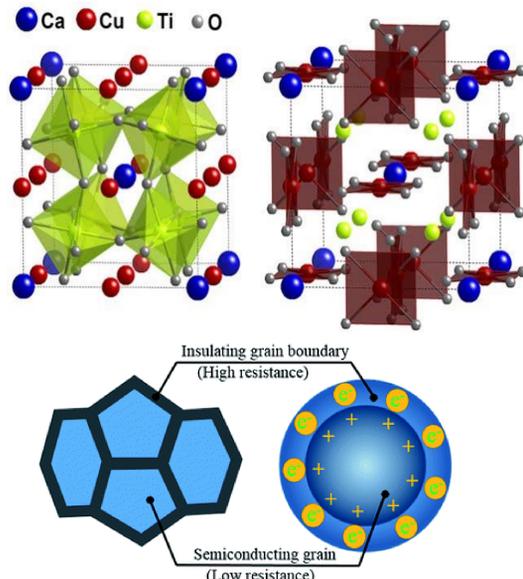
We report enhanced dielectric properties and dielectric relaxation behaviors of $\text{CaCu}_3\text{Ti}_4\text{O}_{12}$ (CCTO) by adopting a novel approach of codoping (Sr,Sb). Structural, microstructural and dielectric properties were investigated in details. Sr substituted in Ca site can effectively suppress the grain growth, further increase in Sb concentration as a codopant shows hike in dielectric constant. Dielectric properties of CCTO are explained in terms of a capacitive-layer model consisting of semiconducting grains and insulating grain boundaries.

Introduction

Technological applications like supercapacitors and electronic devices rely on materials that possess a high dielectric constant, low dissipation, temperature and frequency stability, energy density, charge-discharge cycles, break-down voltage etc.

It shows so called “giant-dielectric phenomenon” or “colossal dielectric constant $\sim 10^4$, which is contrast to ferroelectrics.

Internal barrier layer capacitor (IBLC) model based on Maxwell–Wagner polarization, relates colossal dielectric permittivity (ϵ) to the electrically heterogeneous microstructure.



Experimental

CaCO_3 , CuO , TiO_2 , SrCO_3 , Sb_2O_5
Appropriate weights of starting materials

Homogeneous Mixing with
Agate and Mortar

Calcined at 900°C, 24hrs

Regrinding of Calcined Powder

Powder Pressed into Pellet and
Sintered at 1100°C, 24 hr

A series of samples prepared :
 $\text{CaCu}_3\text{Ti}_4\text{O}_{12}$ as CCTO, $\text{Ca}_{0.9}\text{Sr}_{0.1}\text{Cu}_3\text{Ti}_4\text{O}_{12}$ as CCTO1, $\text{Ca}_{0.9}\text{Sr}_{0.1}\text{Cu}_3\text{Ti}_{3.99}\text{Sb}_{0.01}\text{O}_{12}$ as CCTO2 and $\text{Ca}_{0.9}\text{Sr}_{0.1}\text{Cu}_3\text{Ti}_{3.95}\text{Sb}_{0.05}\text{O}_{12}$ as CCTO3.

Investigation of Phase purity and microstructures by XRD($\text{CuK}\alpha$) and SEM(Jeol, USA)

Coating pellets with silver paint and drying for Impedance Measurement using HIOKI3570 and homemade dielectric cell.

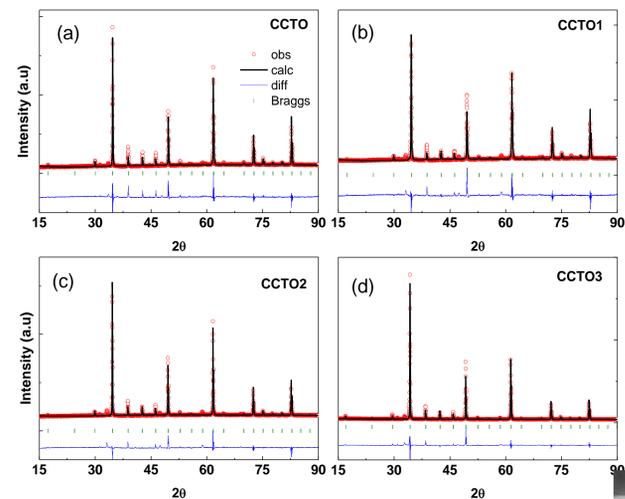
Conclusion

- Dielectric constant of modified CCTO achieved upto several orders by co-doping of Sr, Sb ions.
- Correlation between electrical behavior mainly dielectric relaxation and microstructure reveals that modification affects grain boundary resistance leading to high dielectric constant.
- Giant response is correlated with the potential barrier height at grain boundaries (GBs).

References

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Results and Discussions

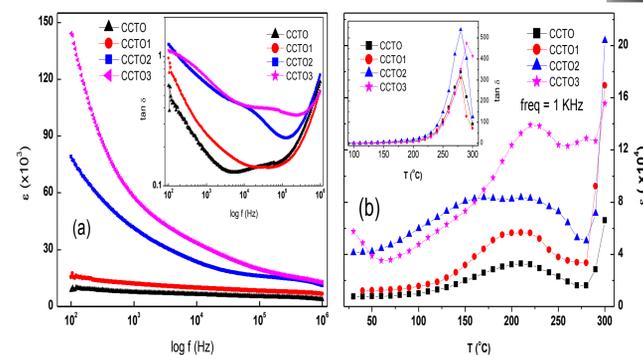
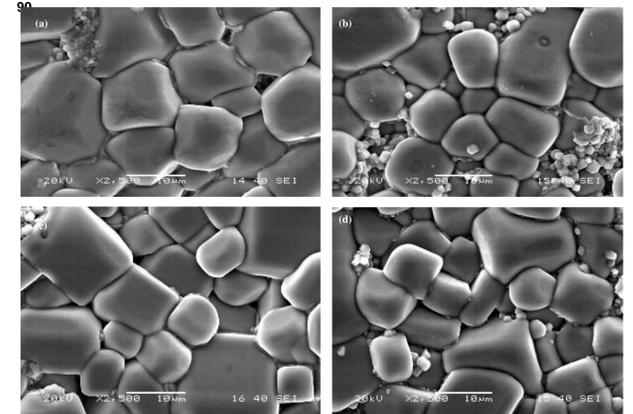


- Quantitative Phase analysis of XRD by Rietveld Method.
- The decrease in lattice parameter with Sr^{2+} and on various concentration of Sb^{5+} might be attributed to variations in ionic radii.

Elements	Wycof. symbol	CCTO	CCTO1 (Sr=10%)	CCTO1 (Sr=10%, Sb=1%)	CCTO2 (Sr=10%, Sb=3%)	CCTO3 (Sr=10%, Sb=5%)
Ca/Sr	x, y, z	0.0, 0.0	0.0, 0.0	0.0, 0.0	0.0, 0.0	0.0, 0.0
Cu	x, y, z	0.0, 0.5, 0.5	0.0, 0.5, 0.5	0.0, 0.5, 0.5	0.0, 0.5, 0.5	0.0, 0.5, 0.5
Ti/Sb	x, y, z	0.25, 0.25, 0.25	0.25, 0.25, 0.25	0.25, 0.25, 0.25	0.25, 0.25, 0.25	0.25, 0.25, 0.25
O	x, y, z	0.2949(5) 0.1810(5) 0	0.2829(4) 0.1773(6) 0	0.3044(2) 0.1663(3) 0	0.2987(6) 0.1866(1) 0	0.2991(7) 0.1863(1) 0
Cell parameter(Å)	a	7.4030(9)	7.4023(2)	7.3958(8)	7.4058(4)	7.3979(4)
Volume(Å ³)	v	405.724	405.303	404.534	406.193	404.895

Mean grain sizes of CCTO, CCTO1, CCTO2 and CCTO3 were found to be 15.61, 12.08, 18.21, 10.04 μm , which indicates the effect of co-doping of Sr and Sb in the microstructure of CCTO.

SEM micrograph shows microstructure has highly compacted grains with grain boundaries.



At low frequency a gigantic change in the permittivity of CCTO3 occurs as compared to the pure CCTO.

Frequency dependence of $\tan\delta$ shows two relaxations, corresponding to DC conduction and primary polarization respectively.

One major semicircular arc in all the plots depicts the presence of grain-boundary effect as the major contributor towards the characteristic dielectric behavior of these ceramics.

Radii of semi-circular arcs at a particular temperature varies on modifications, which may be a consequence of variation in the resistance of grain boundaries.

Activation energy (E_a) of relaxation calculated to be 0.247eV, 0.258eV, 0.186eV and 0.203eV for CCTO, CCTO1, CCTO2 and CCTO3 respectively.

